

ABSTRACT OF THE DISCLOSURE

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The invention is to provide a semiconductor device having a semiconductor circuit comprising a semiconductor element having improved TFT characteristics and uniform characteristics by 5 improving an active layer, particularly an interface between a region forming a channel forming region and a gate insulating film. In the invention in order to attain the object described above, an material for promoting crystallization is added to a substrate or an underlayer film, an initial semiconductor film and a first gate insulating film are 10 continuously formed, crystallization of the initial semiconductor film is conducted by irradiation of an infrared ray or an ultraviolet ray (laser light) through the first gate insulating film, patterning is conducted to obtain an active layer and the first gate insulating film, which have desired shapes, and a second gate insulating film is 15 formed.

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